

Please amend the subject application as follows:

IN THE CLAIMS:

Please cancel claims 5, 15 and 21-27 without prejudice and accept amended claims 1, 6 and 16 as follows:

1. (currently amended) A silicon crystallization system comprising:

a plurality of beam generators each generating a laser beams, each laser beam having substantially the same intensity;

an a plurality of optical units controlling a synthesized beam, wherein the synthesized beam with substantially the same intensity as the intensity of the laser beam is formed by synthesizing the laser beams from the beam generators with a time difference to generate an output beam; and

a plurality of stages for mounting a substrates provided with a silicon layers to be polycrystallized by the output beams from the optical unit.

2. (original) The system of claim 1, wherein a duration of the synthesized beam is longer than each of the laser beams generated by the beam generators.

3. (original) The system of claim 2, further comprising a beam synthesizer generating the synthesized beam.

4. (original) The system of claim 1, further comprising a chamber provided with the optical unit and the stage therein.

5. (canceled)

6. (currently amended) A silicon crystallization system comprising:

a plurality of beam generators each generating a laser beams, each laser beam having substantially the same intensity;

a beam splitter receiving and splitting a synthesized beam into a plurality of beamlets, wherein the synthesized beam with substantially the same intensity as the intensity of the laser beam is formed by synthesizing the laser beams from the beam generators with a time difference into a plurality of beamlets;

a plurality of optical units controlling the beamlets from the beam splitter; and

a plurality of stages for mounting substrates provided with silicon layers to be polycrystallized by the beamlets from the optical units.

7. (original) The system of claim 6, wherein a duration of the synthesized beam is longer than each of the laser beams generated by the beam generators.

8. (original) The system of claim 6, further comprising a beam synthesizer generating the synthesized beam.

9. (original) The system of claim 6, further comprising a plurality of chambers, each chamber provided with one of the optical units and one of the stages therein.

10. (original) The system of claim 9, wherein one of the chambers loads a substrate while another of the chambers performs polycrystallization.

11. (original) The system of claim 9, wherein at least two of the chambers simultaneously performs polycrystallization.

12. (previously presented) The system of claim 10, wherein the polycrystallization comprises sequential lateral solidification (SLS).

13. (previously presented) The system of claim 10, wherein the number of the chambers is three.

14. (previously presented) The system of claim 10, wherein the chambers perform the polycrystallization in turn.

15. (canceled)

16. (currently amended) A silicon crystallization system comprising:

a plurality of beam generators each generating a laser beam, each laser beam having substantially the same intensity;

a beam synthesizer generating a synthesized beam with substantially the same intensity as the intensity of the laser beam from the laser beams generated by the beam generators;

a beam splitter splitting the synthesized ~~laser beam from the beam generator~~
into a plurality of beamlets; and

a plurality of chambers, each chamber including an optical unit controlling one
of the beamlets from the beam splitter and a stage for mounting a substrate
provided with a silicon layer to be polycrystallized by the beamlet from the optical
unit.

17. (original) The system of claim 16, wherein one of the chambers loads a
substrate while another of the chambers performs polycrystallization.

18. (original) The system of claim 16, wherein at least two of the chambers
simultaneously perform polycrystallization.

19. (previously presented) The system of claim 17, wherein the polycrystallization
comprises sequential lateral solidification (SLS).

20. (previously presented) The system of claim 17, wherein the chambers perform
the polycrystallization in turn.

21.-27. (canceled)